



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

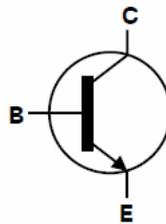
- $BV_{CEO} > 60V$
- $I_C = 3A$ High Continuous Current
- $I_{CM} = 6A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < 300mV @ 1A$
- Complementary PNP Type: DIODES™ NK-FZT751Q

Mechanical Data

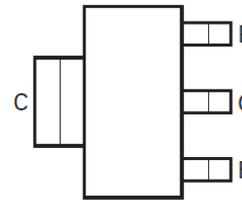
- Package: SOT223 (Type DN)
- Package Material: Molded Plastic. "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208③
- Weight: 0.112 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3	A
Peak Pulse Current	I _{CM}	6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	P _D	(Note 5)	2	W
		(Note 6)	3	W
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	62.5	°C/W
		(Note 6)	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	12.9	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

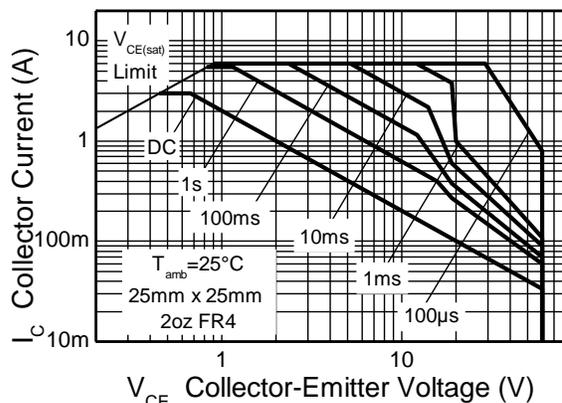


Figure 1. Safe Operating Area

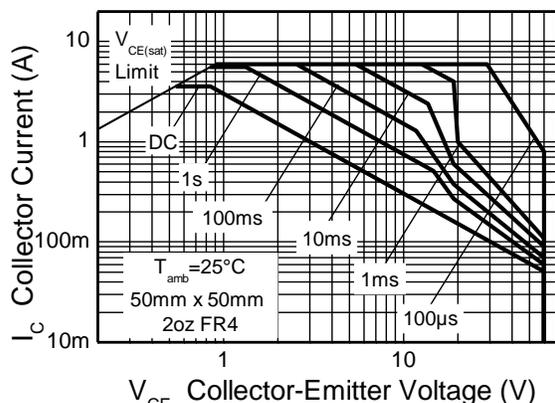


Figure 2. Safe Operating Area

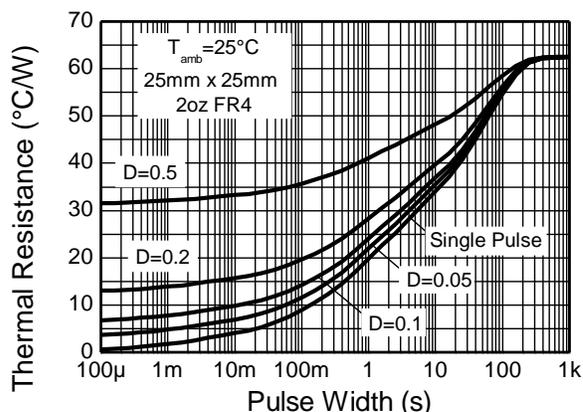


Figure 3. Transient Thermal Impedance

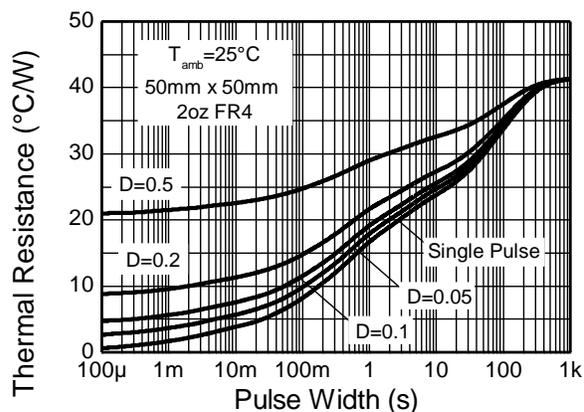


Figure 4. Transient Thermal Impedance

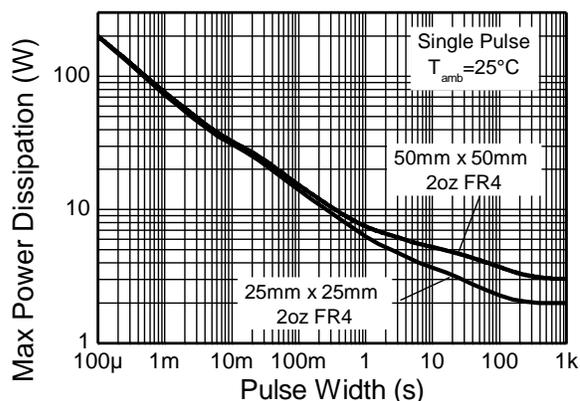


Figure 5. Power Pulse Dissipation

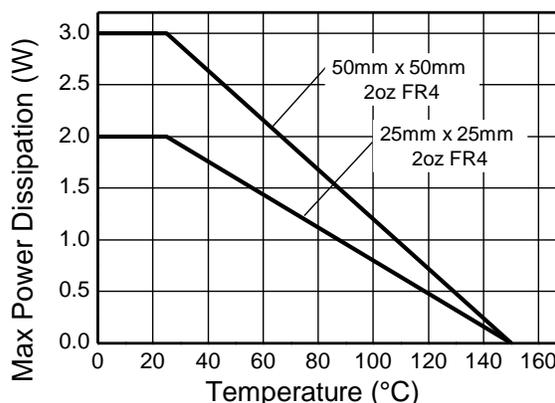


Figure 6. Power Pulse Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	80	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	60	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	$I_E = 100\mu\text{A}$
Collector Cut-off Current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 60\text{V}$
		—	—	10		$V_{CB} = 60\text{V}, T_A = +125^\circ\text{C}$
Emitter Cut-off Current	I_{EBO}	—	—	100	nA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	0.12	0.3	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
		—	0.35	0.6		$I_C = 3\text{A}, I_B = 300\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	0.9	1.25	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	—	0.8	1.0	V	$I_C = 1\text{A}, V_{CE} = 2\text{V}$
DC Current Gain (Note 9)	h_{FE}	70	200	—	—	$I_C = 50\text{mA}, V_{CE} = 2\text{V}$
		100	200	300		$I_C = 500\text{mA}, V_{CE} = 2\text{V}$
		80	170	—		$I_C = 1\text{A}, V_{CE} = 2\text{V}$
		40	80	—		$I_C = 2\text{A}, V_{CE} = 2\text{V}$
Current Gain-Bandwidth Product (Note 9)	f_T	140	175	—	MHz	$V_{CE} = 5\text{V}, I_C = 100\text{mA}, f = 100\text{MHz}$
Switching Times	t_{on}	—	45	—	ns	$I_C = 500\text{mA}, V_{CC} = 10\text{V}, I_{B1} = -I_{B2} = 50\text{mA}$
	t_{off}	—	800	—		
Output Capacitance (Note 9)	C_{obo}	—	—	30	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

 Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

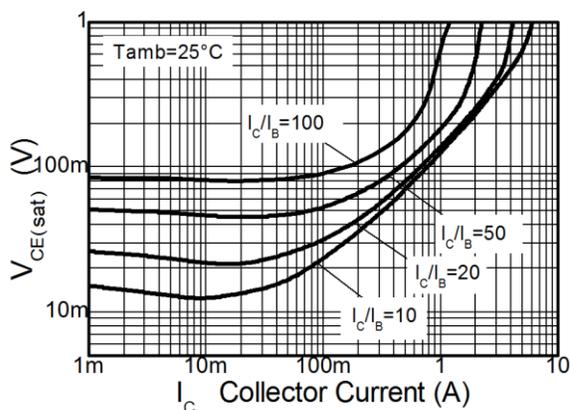


Figure 7. $V_{CE(sat)}$ v I_C

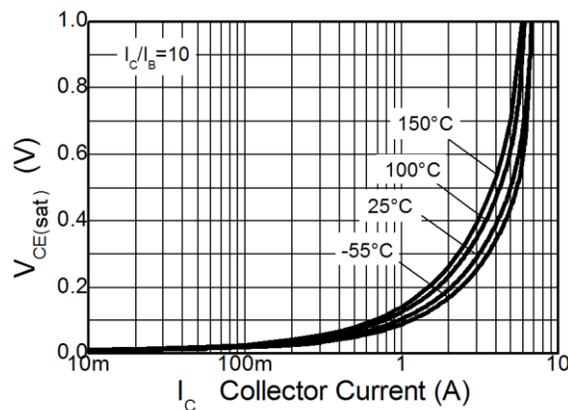


Figure 8. $V_{CE(sat)}$ v I_C

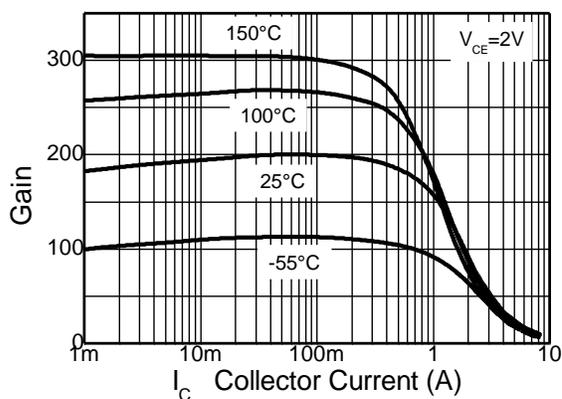


Figure 9. h_{FE} v I_C

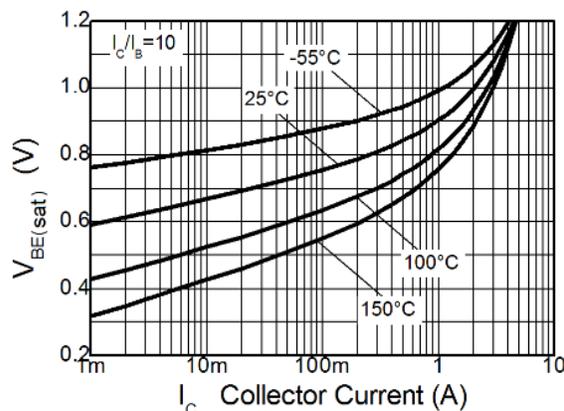


Figure 10. $V_{BE(sat)}$ v I_C

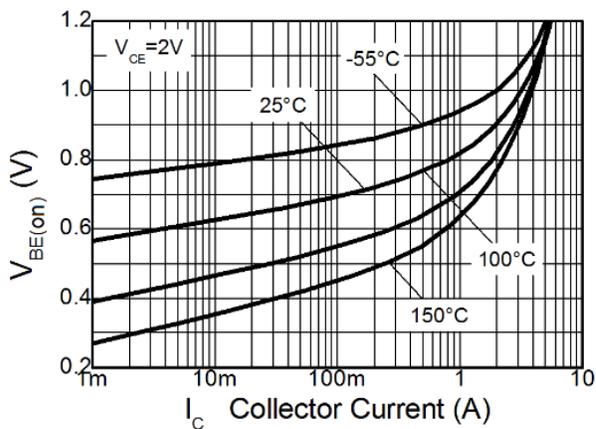
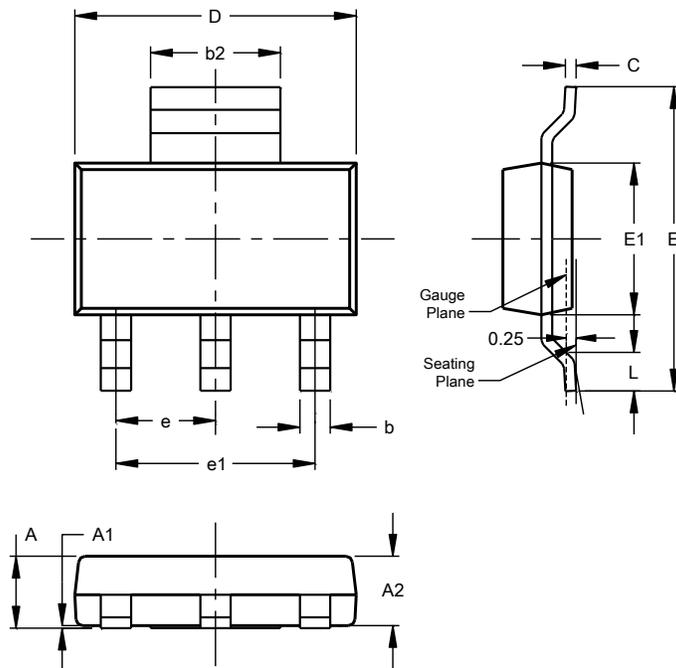


Figure 11. $V_{BE(on)}$ v I_C

Package Outline Dimensions

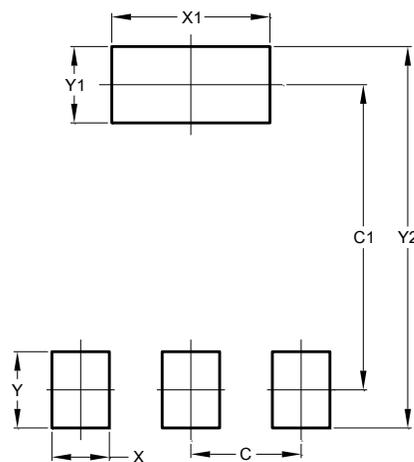
SOT223 (Type DN)



SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00